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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Details	
Product Status	Obsolete
Core Processor	eZ8
Core Size	8-Bit
Speed	20MHz
Connectivity	IrDA, UART/USART
Peripherals	Brown-out Detect/Reset, LED, LVD, POR, PWM, WDT
Number of I/O	17
Program Memory Size	1KB (1K x 8)
Program Memory Type	FLASH
EEPROM Size	16 x 8
RAM Size	256 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 3.6V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	0°C ~ 70°C (TA)
Mounting Type	Through Hole
Package / Case	20-DIP (0.300", 7.62mm)
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/zilog/z8f011aph020sg

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

warning signal. The $\overline{\text{RESET}}$ pin is bidirectional, that is, it functions as reset source and as a reset indicator.

Low-Power Modes

The Z8 Encore! XP F082A Series products contain power-saving features. The highest level of power reduction is provided by the STOP Mode, in which nearly all device functions are powered down. The next lower level of power reduction is provided by the HALT Mode, in which the CPU is powered down.

Further power savings can be implemented by disabling individual peripheral blocks while in Active mode (defined as being in neither STOP nor HALT Mode).

STOP Mode

Executing the eZ8 CPU's STOP instruction places the device into STOP Mode, powering down all peripherals except the Voltage Brown-Out detector, the Low-power Operational Amplifier and the Watchdog Timer. These three blocks may also be disabled for additional power savings. Specifically, the operating characteristics are:

- Primary crystal oscillator and internal precision oscillator are stopped; X_{IN} and X_{OUT} (if previously enabled) are disabled and PA0/PA1 revert to the states programmed by the GPIO registers
- System clock is stopped
- eZ8 CPU is stopped
- Program counter (PC) stops incrementing
- Watchdog Timer's internal RC oscillator continues to operate if enabled by the Oscillator Control Register
- If enabled, the Watchdog Timer logic continues to operate
- If enabled for operation in STOP Mode by the associated Flash option bit, the Voltage Brown-Out protection circuit continues to operate
- Low-power operational amplifier continues to operate if enabled by the Power Control Register
- All other on-chip peripherals are idle

To minimize current in STOP Mode, all GPIO pins that are configured as digital inputs must be driven to one of the supply rails (V_{CC} or GND). Additionally, any GPIOs configured as outputs must also be driven to one of the supply rails. The device can be brought out of STOP Mode using Stop Mode Recovery. For more information about Stop Mode Recovery, see the <u>Reset, Stop Mode Recovery and Low Voltage Detection</u> chapter on page 22.

Port A–D Address Registers

The Port A–D Address registers select the GPIO port functionality accessible through the Port A–D Control registers. The Port A–D Address and Control registers combine to provide access to all GPIO port controls; see Tables 18 and 19.

Bit	7	6	5	4	3	2	1	0	
Field	PADDR[7:0]								
RESET	00H								
R/W	R/W	R/W R/W R/W R/W R/W R/W R/W							
Address	FD0H, FD4H, FD8H, FDCH								

Table 18. Port A–D GPIO Address Registers (PxADDR)

Bit	Description
[]	Port Address
	The Port Address selects one of the subregisters accessible through the Port Control Register. dicates the specific GPIO port pin number (7–0).

Table 19. Port A–D GPIO Address Registers by Bit Description

PADDR[7:0]	Port Control Subregister accessible using the Port A–D Control Registers
00H	No function. Provides some protection against accidental port reconfiguration.
01H	Data Direction.
02H	Alternate Function.
03H	Output Control (Open-Drain).
04H	High Drive Enable.
05H	Stop Mode Recovery Source Enable.
06H	Pull-up Enable.
07H	Alternate Function Set 1.
08H	Alternate Function Set 2.
09H–FFH	No function.

Watchdog Timer

The Watchdog Timer (WDT) protects against corrupt or unreliable software, power faults and other system-level problems which may place the Z8 Encore! XP F082A Series devices into unsuitable operating states. The features of Watchdog Timer include:

- On-chip RC oscillator
- A selectable time-out response: reset or interrupt
- 24-bit programmable time-out value

Operation

The Watchdog Timer is a one-shot timer that resets or interrupts the Z8 Encore! XP F082A Series devices when the WDT reaches its terminal count. The Watchdog Timer uses a dedicated on-chip RC oscillator as its clock source. The Watchdog Timer operates in only two modes: ON and OFF. Once enabled, it always counts and must be refreshed to prevent a time-out. Perform an enable by executing the WDT instruction or by setting the WDT_AO Flash option bit. The WDT_AO bit forces the Watchdog Timer to operate immediately upon reset, even if a WDT instruction has not been executed.

The Watchdog Timer is a 24-bit reloadable downcounter that uses three 8-bit registers in the eZ8 CPU register space to set the reload value. The nominal WDT time-out period is described by the following equation:

WDT Time-out Period (ms) = $\frac{\text{WDT Reload Value}}{10}$

where the WDT reload value is the decimal value of the 24-bit value given by {WDTU[7:0], WDTH[7:0], WDTL[7:0]} and the typical Watchdog Timer RC oscillator frequency is 10kHz. The Watchdog Timer cannot be refreshed after it reaches 000002H. The WDT reload value must not be set to values below 000004H. Table 58 provides information about approximate time-out delays for the minimum and maximum WDT reload values.

WDT Reload Value	WDT Reload Value		e Time-Out Delay VDT oscillator frequency)
(Hex)	(Decimal)	Typical	Description
000004	4	400 μs	Minimum time-out delay
FFFFF	16,777,215	28 minutes	Maximum time-out delay

Table 58. Watchdog Timer Approximate Time-Out Delays

Rate Generator to function as an additional counter if the UART functionality is not employed.

UART Baud Rate Generator

The UART Baud Rate Generator creates a lower frequency baud rate clock for data transmission. The input to the Baud Rate Generator is the system clock. The UART Baud Rate High and Low Byte registers combine to create a 16-bit baud rate divisor value (BRG[15:0]) that sets the data transmission rate (baud rate) of the UART. The UART data rate is calculated using the following equation:

UART Data Rate (bits/s) = $\frac{\text{System Clock Frequency (Hz)}}{16 \times \text{UART Baud Rate Divisor Value}}$

When the UART is disabled, the Baud Rate Generator functions as a basic 16-bit timer with an interrupt upon time-out. Observe the following steps to configure the Baud Rate Generator as a timer with an interrupt upon time-out:

- 1. Disable the UART by clearing the REN and TEN bits in the UART Control 0 Register to 0.
- 2. Load the acceptable 16-bit count value into the UART Baud Rate High and Low Byte registers.
- 3. Enable the Baud Rate Generator timer function and associated interrupt by setting the BRGCTL bit in the UART Control 1 Register to 1.

When configured as a general purpose timer, the interrupt interval is calculated using the following equation:

Interrupt Interval(s) = System Clock Period (s) \times BRG[15:0]

UART Control Register Definitions

The UART Control registers support the UART and the associated Infrared Encoder/ Decoders. For more information about infrared operation, see the <u>Infrared Encoder/</u><u>Decoder</u> chapter on page 120.

UART Control 0 and Control 1 Registers

The UART Control 0 (UxCTL0) and Control 1 (UxCTL1) registers, shown in Tables 63 and 64, configure the properties of the UART's transmit and receive operations. The UART Control registers must not be written while the UART is enabled.

Acceptable Rate (kHz)	BRG Divisor (Decimal)	Actual Rate (kHz)	Error (%)	Acceptable Rate (kHz)	BRG Divisor (Decimal)	Actual Rate (kHz)	Error (%)
1250.0	N/A	N/A	N/A	1250.0	N/A	N/A	N/A
625.0	N/A	N/A	N/A	625.0	N/A	N/A	N/A
250.0	1	223.72	-10.51	250.0	N/A	N/A	N/A
115.2	2	111.9	-2.90	115.2	1	115.2	0.00
57.6	4	55.9	-2.90	57.6	2	57.6	0.00
38.4	6	37.3	-2.90	38.4	3	38.4	0.00
19.2	12	18.6	-2.90	19.2	6	19.2	0.00
9.60	23	9.73	1.32	9.60	12	9.60	0.00
4.80	47	4.76	-0.83	4.80	24	4.80	0.00
2.40	93	2.41	0.23	2.40	48	2.40	0.00
1.20	186	1.20	0.23	1.20	96	1.20	0.00
0.60	373	0.60	-0.04	0.60	192	0.60	0.00
0.30	746	0.30	-0.04	0.30	384	0.30	0.00

Table 72. UART Baud Rates (Continued)

Bit	Description (Continued)
[5:2]	Internal Reference Voltage Level
REFLVL	This reference is independent of the ADC voltage reference. Note: 8-pin devices contain two
	additional LSBs for increased resolution.
	For 20-/28-pin devices:
	0000 = 0.0 V
	0001 = 0.2 V
	0010 = 0.4 V
	0011 = 0.6 V
	0100 = 0.8 V
	0101 = 1.0 V (Default)
	0110 = 1.2 V
	0111 = 1.4 V
	1000 = 1.6 V
	1001 = 1.8 V
	1010–1111 = Reserved

8KB Flash Program Memor	y Addresses (hex) T 1FFF	4KB Flash Program Memory	/ Addresses (hex) 1 0FFF	2KB Flash Program Memory Addresse	s (hex)
Sector 7	1C00	Sector 7	0E00	Sector 3	07FF 0600 05FF
Sector 6	1BFF	Sector 6	0DFF		0400 03FF
	1800 17FF	October 5	0C00 0BFF	Sector 1	0200 01FF
Sector 5	1400 13FF	Sector 5	0A00 09FF	Sector 0	0000
Sector 4	1000	Sector 4	0800		
Sector 3	0FFF 0C00	Sector 3	07FF 0600	1 KB Flash Program Memory	(1)
Sector 2	0BFF 0800	Sector 2	05FF 0400	Addresse Sector 1	es (nex) 03FF 0200
Sector 1	07FF 0400	Sector 1	03FF 0200	Sector 0	01FF
Sector 0	03FF 0000	Sector 0	01FF 0000		

Figure 21. Flash Memory Arrangement

Flash Information Area

The Flash information area is separate from Program Memory and is mapped to the address range FE00H to FFFFH. This area is readable but cannot be erased or overwritten. Factory trim values for the analog peripherals are stored here. Factory calibration data for the ADC is also stored here.

Operation

The Flash Controller programs and erases Flash memory. The Flash Controller provides the proper Flash controls and timing for Byte Programming, Page Erase and Mass Erase of Flash memory.

The Flash Controller contains several protection mechanisms to prevent accidental programming or erasure. These mechanism operate on the page, sector and full-memory levels.

Flash Operation Timing Using the Flash Frequency Registers

Before performing either a program or erase operation on Flash memory, you must first configure the Flash Frequency High and Low Byte registers. The Flash Frequency registers allow programming and erasing of the Flash with system clock frequencies ranging from 32kHz (32768Hz) through 20MHz.

The Flash Frequency High and Low Byte registers combine to form a 16-bit value, FFREQ, to control timing for Flash program and erase operations. The 16-bit binary Flash Frequency value must contain the system clock frequency (in kHz). This value is calculated using the following equation:

 $FFREQ[15:0] = \frac{System Clock Frequency (Hz)}{1000}$

Caution: Flash programming and erasure are not supported for system clock frequencies below 32kHz (32768Hz) or above 20MHz. The Flash Frequency High and Low Byte registers must be loaded with the correct value to ensure operation of the Z8 Encore! XP F082A Series devices.

Flash Code Protection Against External Access

The user code contained within the Flash memory can be protected against external access by the on-chip debugger. Programming the FRP Flash option bit prevents reading of the user code with the On-Chip Debugger. See the <u>Flash Option Bits</u> chapter on page 159 and the <u>On-Chip Debugger</u> chapter on page 180 for more information.

Flash Code Protection Against Accidental Program and Erasure

The Z8 Encore! XP F082A Series provides several levels of protection against accidental program and erasure of the Flash memory contents. This protection is provided by a combination of the Flash option bits, the register locking mechanism, the page select redundancy and the sector level protection control of the Flash Controller.

Flash Code Protection Using the Flash Option Bits

The FRP and FWP Flash option bits combine to provide three levels of Flash Program Memory protection, as shown in Table 79. See the <u>Flash Option Bits</u> chapter on page 159 for more information.

Bit	Description (Continued)
[5:4] OSC_SEL[1:0]	 Oscillator Mode Selection 00 = On-chip oscillator configured for use with external RC networks (<4MHz). 01 = Minimum power for use with very low frequency crystals (32kHz to 1.0MHz). 10 = Medium power for use with medium frequency crystals or ceramic resonators (0.5MHz to 5.0MHz). 11 = Maximum power for use with high frequency crystals (5.0MHz to 20.0MHz). This setting is the default for unprogrammed (erased) Flash.
[3] VBO_AO	 Voltage Brown-Out Protection Always On 0 = Voltage Brown-Out Protection can be disabled in STOP Mode to reduce total power consumption. For the block to be disabled, the power control register bit must also be written (see the <u>Power Control Register Definitions</u> section on page 33). 1 = Voltage Brown-Out Protection is always enabled including during STOP Mode. This setting is the default for unprogrammed (erased) Flash.
[2] FRP	 Flash Read Protect 0 = User program code is inaccessible. Limited control features are available through the On-Chip Debugger. 1 = User program code is accessible. All On-Chip Debugger commands are enabled. This setting is the default for unprogrammed (erased) Flash.
[1]	Reserved This bit is reserved and must be programmed to 1.
[0] FWP	 Flash Write Protect This Option Bit provides Flash Program Memory protection: 0 = Programming and erasure disabled for all of Flash Program Memory. Programming, Page Erase and Mass Erase through User Code is disabled. Mass Erase is available using the On-Chip Debugger. 1 = Programming, Page Erase and Mass Erase are enabled for all of Flash program memory.

Nonvolatile Data Storage

The Z8 Encore! XP F082A Series devices contain a nonvolatile data storage (NVDS) element of up to 128 bytes. This memory can perform over 100,000 write cycles.

Operation

The NVDS is implemented by special purpose Zilog software stored in areas of program memory, which are not user-accessible. These special-purpose routines use the Flash memory to store the data. The routines incorporate a dynamic addressing scheme to maximize the write/erase endurance of the Flash.

Note: Different members of the Z8 Encore! XP F082A Series feature multiple NVDS array sizes; see the <u>Part Selection Guide</u> section on page 2 for details. Devices containing 8KB of Flash memory do not include the NVDS feature.

NVDS Code Interface

Two routines are required to access the NVDS: a write routine and a read routine. Both of these routines are accessed with a CALL instruction to a predefined address outside of the user-accessible program memory. Both the NVDS address and data are single-byte values. Because these routines disturb the working register set, user code must ensure that any required working register values are preserved by pushing them onto the stack or by changing the working register pointer just prior to NVDS execution.

During both read and write accesses to the NVDS, interrupt service is NOT disabled. Any interrupts that occur during the NVDS execution must take care not to disturb the working register and existing stack contents or else the array may become corrupted. Disabling interrupts before executing NVDS operations is recommended.

Use of the NVDS requires 15 bytes of available stack space. Also, the contents of the working register set are overwritten.

For correct NVDS operation, the Flash Frequency registers must be programmed based on the system clock frequency (see **the** <u>Flash Operation Timing Using the Flash Frequency</u> <u>Registers</u> **section on page 149**).

Byte Read

To read a byte from the NVDS array, user code must first push the address onto the stack. User code issues a CALL instruction to the address of the byte-read routine (0×1000) . At the return from the sub-routine, the read byte resides in working register R0 and the read status byte resides in working register R1. The contents of the status byte are undefined for read operations to illegal addresses. Also, the user code must pop the address byte off the stack.

The read routine uses 9 bytes of stack space in addition to the one byte of address pushed by the user. Sufficient memory must be available for this stack usage.

Because of the Flash memory architecture, NVDS reads exhibit a nonuniform execution time. A read operation takes between 44 μ s and 489 μ s (assuming a 20MHz system clock). Slower system clock speeds result in proportionally higher execution times.

NVDS byte reads from invalid addresses (those exceeding the NVDS array size) return 0xff. Illegal read operations have a 2 μ s execution time.

The status byte returned by the NVDS read routine is zero for successful read, as determined by a CRC check. If the status byte is nonzero, there was a corrupted value in the NVDS array at the location being read. In this case, the value returned in R0 is the byte most recently written to the array that does not have a CRC error.

Power Failure Protection

The NVDS routines employ error checking mechanisms to ensure a power failure endangers only the most recently written byte. Bytes previously written to the array are not perturbed.

A system reset (such as a pin reset or Watchdog Timer reset) that occurs during a write operation also perturbs the byte currently being written. All other bytes in the array are unperturbed.

Optimizing NVDS Memory Usage for Execution Speed

NVDS read time can vary drastically. This discrepancy is a trade-off for minimizing the frequency of writes that require post-write page erases, as indicated in Table 107. The NVDS read time of address N is a function of the number of writes to addresses other than N since the most recent write to address N, plus the number of writes since the most recent page erase. Neglecting effects caused by page erases and results caused by the initial condition in which the NVDS is blank, a rule of thumb is that every write since the most recent page erase causes read times of unwritten addresses to increase by 1 µs up to a maximum of (511-NVDS_SIZE)µs.

DBG \leftarrow Size[15:8] DBG \leftarrow Size[7:0] DBG \leftarrow 1-65536 data bytes

Read Data Memory (0DH). The Read Data Memory command reads from Data Memory. This command is equivalent to the LDE and LDEI instructions. Data can be read 1 to 65536 bytes at a time (65536 bytes can be read by setting size to 0). If the device is not in DEBUG Mode, this command returns FFH for the data.

```
DBG \leftarrow 0DH
DBG \leftarrow Data Memory Address[15:8]
DBG \leftarrow Data Memory Address[7:0]
DBG \leftarrow Size[15:8]
DBG \leftarrow Size[7:0]
DBG \rightarrow 1-65536 data bytes
```

Read Program Memory CRC (0EH). The Read Program Memory CRC command computes and returns the Cyclic Redundancy Check (CRC) of Program Memory using the 16bit CRC-CCITT polynomial. If the device is not in DEBUG Mode, this command returns FFFFH for the CRC value. Unlike most other OCD Read commands, there is a delay from issuing of the command until the OCD returns the data. The OCD reads the Program Memory, calculates the CRC value and returns the result. The delay is a function of the Program Memory size and is approximately equal to the system clock period multiplied by the number of bytes in the Program Memory.

DBG \leftarrow 0EH DBG \rightarrow CRC[15:8] DBG \rightarrow CRC[7:0]

Step Instruction (10H). The Step Instruction command steps one assembly instruction at the current Program Counter (PC) location. If the device is not in DEBUG Mode or the Flash Read Protect Option bit is enabled, the OCD ignores this command.

DBG \leftarrow 10H

Stuff Instruction (11H). The Stuff Instruction command steps one assembly instruction and allows specification of the first byte of the instruction. The remaining 0-4 bytes of the instruction are read from Program Memory. This command is useful for stepping over instructions where the first byte of the instruction has been overwritten by a Breakpoint. If the device is not in DEBUG Mode or the Flash Read Protect Option bit is enabled, the OCD ignores this command.

DBG ← 11H DBG ← opcode[7:0]

Execute Instruction (12H). The Execute Instruction command allows sending an entire instruction to be executed to the eZ8 CPU. This command can also step over Breakpoints. The number of bytes to send for the instruction depends on the opcode. If the device is not

Assembly Language Source Program Example

JP START	; Everything after the semicolon is a comment.
START:	; A label called 'START'. The first instruction (JP START) in this ; example causes program execution to jump to the point within the ; program where the START label occurs.
LD R4, R7	; A Load (LD) instruction with two operands. The first operand, ; Working Register R4, is the destination. The second operand, ; Working Register R7, is the source. The contents of R7 is ; written into R4.
LD 234H, #%01	; Another Load (LD) instruction with two operands. ; The first operand, Extended Mode Register Address 234H, ; identifies the destination. The second operand, Immediate Data ; value 01H, is the source. The value 01H is written into the ; Register at address 234H.

Assembly Language Syntax

For proper instruction execution, eZ8 CPU assembly language syntax requires that the operands be written as 'destination, source'. After assembly, the object code usually has the operands in the order 'source, destination', but ordering is opcode-dependent. The following instruction examples illustrate the format of some basic assembly instructions and the resulting object code produced by the assembler. This binary format must be followed if manual program coding is preferred or if you intend to implement your own assembler.

Example 1. If the contents of registers 43H and 08H are added and the result is stored in 43H, the assembly syntax and resulting object code is:

Assembly Language Code	ADD	43H,	08H	(ADD dst, src)
Object Code	04	08	43	(OPC src, dst)

Example 2. In general, when an instruction format requires an 8-bit register address, that address can specify any register location in the range 0–255 or, using Escaped Mode Addressing, a Working Register R0–R15. If the contents of Register 43H and Working Register R8 are added and the result is stored in 43H, the assembly syntax and resulting object code is:

Assembly Language Code	ADD	43H,	R8	(ADD dst, src)
Object Code	04	E8	43	(OPC src, dst)

Mnemonic	Operands	Instruction
BCLR	bit, dst	Bit Clear
BIT	p, bit, dst	Bit Set or Clear
BSET	bit, dst	Bit Set
BSWAP	dst	Bit Swap
CCF	—	Complement Carry Flag
RCF	—	Reset Carry Flag
SCF	—	Set Carry Flag
ТСМ	dst, src	Test Complement Under Mask
ТСМХ	dst, src	Test Complement Under Mask using Extended Addressing
ТМ	dst, src	Test Under Mask
TMX	dst, src	Test Under Mask using Extended Addressing

Table 121. Bit Manipulation Instructions

Table 122. Block Transfer Instructions

Mnemonic	Operands	Instruction
LDCI	dst, src	Load Constant to/from Program Memory and Auto- Increment Addresses
LDEI	dst, src	Load External Data to/from Data Memory and Auto- Increment Addresses

Table 123. CPU Control Instructions

Mnemonic	Operands	Instruction
ATM		Atomic Execution
CCF	—	Complement Carry Flag
DI	—	Disable Interrupts
EI	—	Enable Interrupts
HALT	—	Halt Mode
NOP	—	No Operation

Assembly			ress ode	_ Opcode(s)			Fla	ags			Fetch Cycle	Instr. Cycle
Mnemonic	Symbolic Operation	dst	src	(Hex)	С	Ζ	S	۷	D	Н	S	S
CALL dst	$SP \leftarrow SP - 2$	IRR		D4	_	_	_	_	-	_	2	6
	@SP ← PC PC ← dst	DA		D6	-						3	3
CCF	$C \leftarrow \sim C$			EF	*	-	_	-	-		1	2
CLR dst	dst ← 00H	R		B0	-	_	_	-	_	_	2	2
		IR		B1	-						2	3
COM dst	dst ← ~dst	R		60	_	*	*	0	_	_	2	2
		IR		61	-						2	3
CP dst, src	dst - src	r	r	A2	*	*	*	*	_	_	2	3
		r	Ir	A3	-						2	4
		R	R	A4	-						3	3
		R	IR	A5	-						3	4
		R	IM	A6	-						3	3
		IR	IM	A7	-						3	4
CPC dst, src	dst - src - C	r	r	1F A2	*	*	*	*	_	_	3	3
		r	Ir	1F A3	-						3	4
		R	R	1F A4	-						4	3
		R	IR	1F A5	-						4	4
		R	IM	1F A6	-						4	3
		IR	IM	1F A7	-						4	4
CPCX dst, src	dst - src - C	ER	ER	1F A8	*	*	*	*	_	_	5	3
		ER	IM	1F A9	-						5	3
CPX dst, src	dst - src	ER	ER	A8	*	*	*	*	_	_	4	3
		ER	IM	A9	-						4	3

Table 128. eZ8 CPU Instruction Summary (Continued)

Note: Flags Notation:

* = Value is a function of the result of the operation.

- = Unaffected.

X = Undefined.

0 = Reset to 0.

1 =Set to 1.

			T _A = -40°C to +105°C (unless otherwise specified)				
Symbol	Parameter	Minimum	Typical	Maximum	Units	Conditions	
V _{OH1}	High Level Output Voltage	2.4	-	_	V	I _{OH} = -2 mA; V _{DD} = 3.0 V High Output Drive disabled.	
V _{OL2}	Low Level Output Voltage	_	-	0.6	V	$I_{OL} = 20 \text{ mA}; V_{DD} = 3.3 \text{ V}$ High Output Drive enabled.	
V _{OH2}	High Level Output Voltage	2.4	_	_	V	I _{OH} = -20 mA; V _{DD} = 3.3V High Output Drive enabled.	
I _{IH}	Input Leakage Cur- rent	-	<u>+</u> 0.002	<u>+</u> 5	μA	$V_{IN} = V_{DD}$ $V_{DD} = 3.3 V;$	
IIL	Input Leakage Cur- rent	-	<u>+</u> 0.007	<u>+</u> 5	μA	$V_{IN} = V_{SS}$ $V_{DD} = 3.3V;$	
I _{TL}	Tristate Leakage Current	-	-	<u>+</u> 5	μA		
I _{LED}	Controlled Current	1.8	3	4.5	mA	$\{AFS2, AFS1\} = \{0, 0\}$	
	Drive	2.8	7	10.5	mA	$\{AFS2, AFS1\} = \{0, 1\}$	
		7.8	13	19.5	mA	${AFS2,AFS1} = {1,0}$	
		12	20	30	mA	${AFS2,AFS1} = {1,1}$	
C _{PAD}	GPIO Port Pad Capacitance	-	8.0 ²	-	pF		
C _{XIN}	XIN Pad Capaci- tance	-	8.0 ²	-	pF		
C _{XOUT}	X _{OUT} Pad Capaci- tance	-	9.5 ²	_	pF		
I _{PU}	Weak Pull-up Cur- rent	30	100	350	μA	V _{DD} = 3.0 V–3.6 V	
V _{RAM}	RAM Data Reten- tion Voltage	TBD			V	Voltage at which RAM retains static values; no reading or writing is allowed.	

Table 131. DC Characteristics (Continued)

Notes:

1. This condition excludes all pins that have on-chip pull-ups, when driven Low.

2. These values are provided for design guidance only and are not tested in production.

AC Characteristics

The section provides information about the AC characteristics and timing. All AC timing information assumes a standard load of 50pF on all outputs.

		T _A = -40°C (unless c	℃ to 3.6V c to +105°C otherwise ted)		
Symbol	Parameter	Minimum	Maximum	Units	Conditions
F _{SYSCLK}	System Clock Frequency	-	20.0	MHz	Read-only from Flash mem- ory
		0.032768	20.0	MHz	Program or erasure of the Flash memory
F _{XTAL}	Crystal Oscillator Frequency	-	20.0	MHz	System clock frequencies below the crystal oscillator minimum require an exter- nal clock driver
T _{XIN}	System Clock Period	50	-	ns	T _{CLK} = 1/F _{sysclk}
T _{XINH}	System Clock High Time	20	30	ns	T _{CLK} = 50 ns
T _{XINL}	System Clock Low Time	20	30	ns	T _{CLK} = 50 ns
T _{XINR}	System Clock Rise Time	-	3	ns	T _{CLK} = 50 ns
T _{XINF}	System Clock Fall Time	_	3	ns	T _{CLK} = 50 ns

Table 134. Internal Precision Oscillator Electrical Characteristics

		T _A = -	= 2.7V to -40°C to + otherwise			
Symbol	Parameter	Minimum	Typical	Maximum	Units	Conditions
F _{IPO}	Internal Precision Oscillator Fre- quency (High Speed)		5.53		MHz	$V_{DD} = 3.3 V$ $T_A = 30^{\circ}C$
F _{IPO}	Internal Precision Oscillator Fre- quency (Low Speed)		32.7		kHz	$V_{DD} = 3.3 V$ $T_A = 30^{\circ}C$
F _{IPO}	Internal Precision Oscillator Error		<u>+</u> 1	<u>+</u> 4	%	
T _{IPOST}	Internal Precision Oscillator Startup Time		3		μs	

		T _A :	= 3.0 V to = 0°C to +7 otherwise	′0°C			
Symbol	Parameter	Minimum	Typical	Maximum	Units	Conditions	
	Resolution	10		_	bits		
	Differential Nonlinearity (DNL)	-1.0	-	1.0	LSB ³	External V _{REF} = 2.0 V; R _S \leftarrow 3.0 k Ω	
	Integral Nonlinearity (INL)	-3.0	-	3.0	LSB ³	External V _{REF} = 2.0 V; R _S \leftarrow 3.0 k Ω	
	Offset Error with Calibra- tion		<u>+</u> 1		LSB ³		
	Absolute Accuracy with Calibration		<u>+</u> 3		LSB ³		
V _{REF}	Internal Reference Volt- age	1.0 2.0	1.1 2.2	1.2 2.4	V	REFSEL=01 REFSEL=10	
V _{REF}	Internal Reference Varia- tion with Temperature		<u>+</u> 1.0		%	Temperature variation with $V_{DD} = 3.0$	
V _{REF}	Internal Reference Volt- age Variation with V _{DD}		<u>+</u> 0.5		%	Supply voltage varia- tion with $T_A = 30^{\circ}C$	
R _{RE-} FOUT	Reference Buffer Output Impedance		850		W	When the internal ref- erence is buffered and driven out to the VREF pin (REFOUT = 1)	
	Single-Shot Conversion Time	-	5129	_	Sys- tem clock cycles	All measurements but temperature sensor	
			10258			Temperature sensor measurement	

Table 139. Analog-to-Digital Converter Electrical Characteristics and Timing

Notes:

1. Analog source impedance affects the ADC offset voltage (because of pin leakage) and input settling time.

2. Devices are factory calibrated at V_{DD} = 3.3V and T_A = +30°C, so the ADC is maximally accurate under these conditions.

3. LSBs are defined assuming 10-bit resolution.

4. This is the maximum recommended resistance seen by the ADC input pin.

5. The input impedance is inversely proportional to the system clock frequency.

Part Number	Flash	RAM	NVDS	I/O Lines	Interrupts	16-Bit Timers w/PWM	10-Bit A/D Channels	UART with IrDA	Comparator	Temperature Sensor	Description
Z8 Encore! XP F082A Series with 8KB Flash											
Standard Temperatu											
Z8F081APB020SG	8KB	1KB	0	6	13	2	0	1	1	0	PDIP 8-pin package
Z8F081AQB020SG	8KB	1KB	0	6	13	2	0	1	1	0	QFN 8-pin package
Z8F081ASB020SG	8KB	1KB	0	6	13	2	0	1	1	0	SOIC 8-pin package
Z8F081ASH020SG	8KB	1KB	0	17	19	2	0	1	1	0	SOIC 20-pin package
Z8F081AHH020SG	8KB	1KB	0	17	19	2	0	1	1	0	SSOP 20-pin package
Z8F081APH020SG	8KB	1KB	0	17	19	2	0	1	1	0	PDIP 20-pin package
Z8F081ASJ020SG	8KB	1KB	0	25	19	2	0	1	1	0	SOIC 28-pin package
Z8F081AHJ020SG	8KB	1KB	0	25	19	2	0	1	1	0	SSOP 28-pin package
Z8F081APJ020SG	8KB	1KB	0	25	19	2	0	1	1	0	PDIP 28-pin package
Extended Temperature: –40°C to 105°C											
Z8F081APB020EG	8KB	1KB	0	6	13	2	0	1	1	0	PDIP 8-pin package
Z8F081AQB020EG	8KB	1KB	0	6	13	2	0	1	1	0	QFN 8-pin package
Z8F081ASB020EG	8KB	1KB	0	6	13	2	0	1	1	0	SOIC 8-pin package
Z8F081ASH020EG	8KB	1KB	0	17	19	2	0	1	1	0	SOIC 20-pin package
Z8F081AHH020EG	8KB	1KB	0	17	19	2	0	1	1	0	SSOP 20-pin package
Z8F081APH020EG	8KB	1KB	0	17	19	2	0	1	1	0	PDIP 20-pin package
Z8F081ASJ020EG	8KB	1KB	0	25	19	2	0	1	1	0	SOIC 28-pin package
Z8F081AHJ020EG	8KB	1KB	0	25	19	2	0	1	1	0	SSOP 28-pin package
Z8F081APJ020EG	8KB	1KB	0	25	19	2	0	1	1	0	PDIP 28-pin package

Table 148. Z8 Encore! XP F082A Series Ordering Matrix